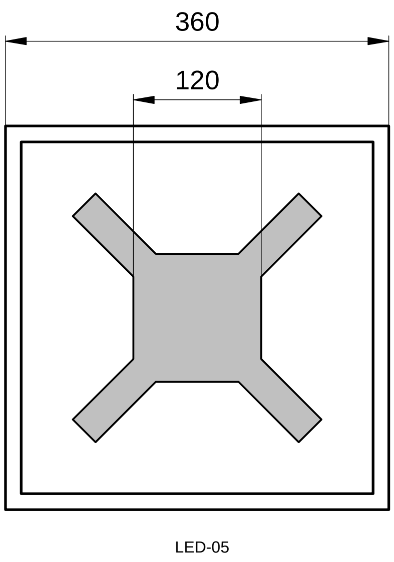
LED - Chip ELC-770-27

15.02.2012 rev. 08

Radiation	Type	Technology	Electrodes
Infrared	DDH	AlGaAs/AlGaAs	N (cathode) up



typ. dimensions (µm)

typ. thickness

150 (±25) µm

cathode

gold alloy, 1.5 µm

anode

gold alloy, 0.5 µm,
structured, 25% covered

Maximum Ratings

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward current (DC)		I_F			50	mA

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F = 20 mA	V_F	1.6	1.8	2.0	V
Reverse voltage	I_R = 100 µA	V_R	5			V
Radiant power[1]	I_F = 20 mA	Φ_e	2.5	3.5		mW
Peak wavelength	I_F = 20 mA	λ_p	760	770	780	nm
Spectral bandwidth at 50%	I_F = 20 mA	$\Delta\lambda_{0.5}$	20	30	40	nm
Switching time	I_F = 20 mA	t_r, t_f		40	100	ns

[1] Measured on bare chip on TO-18 header with JENOPTIK Polymer Systems equipment

Labeling

Type	Lot N°	Φ_e(typ) [mW]	V_F(typ) [V]	Quantity
ELC-770-27				

Packing: Chips on adhesive film with wire-bond side on top